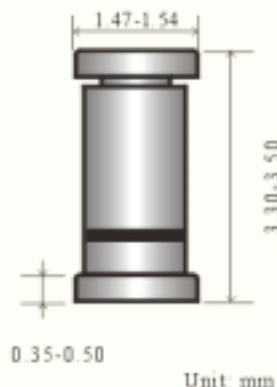




LL-34 GLASS



**LL-34(Mini-melf)玻璃封装二极管**  
**LL-34(Mini-melf) Glass Switching Diode**

**特征 Features**

- 开关速度小于 50nS; Fast Switching Device (TRR <50 nS)
- 最大功率耗散 400mW; Power Dissipation of 400mW
- 高稳定性和可靠性。High Stability and High Reliability
- 反向漏电流小。Low reverse leakage

**机械数据 Mechanical Data**

- 封装: LL-34 玻璃封装 Case: LL-34 Glass Case
- 极性: 色环端为负极 Polarity: Color band denotes cathode end
- 安装位置: 任意 Mounting Position: Any

**极限值和温度特性**( $T_A = 25$  除非另有规定)

**Maximum Ratings & Thermal Characteristics** (Ratings at 25 ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value				单位 Unit
		BAV100	BAV101	BAV102	BAV103	
反向电压 Reverse Voltage	$V_R$	50	100	150	200	V
最大反向电压 Maximum Repetitive Reverse Voltage	$V_{RRM}$	60	120	200	250	V
功率消耗 Power Dissipation	$P_d$	400				mW
工作结温 Operating junction temperature	$T_j$	175				
存储温度 Storage temperature range	$T_s$	-65+175				
直流正向电流 Forward DC Current at ( $T_A = 25$ )	$I_F$	250				mA
平均正向电流 Average Forward Current( $T_A=25$ & f 50Hz)	$I_{F(AV)}$	200				mA
正向重复电流 Repetitive Peak Forward Current	$I_{FRM}$	625				mA
正向(不重复)浪涌电流 Peak Forward Surge Current @ $t_p=1s; T_A=25$	$I_{FSM}$	1.0				A

**电特性** ( $T_A = 25$  除非另有规定)

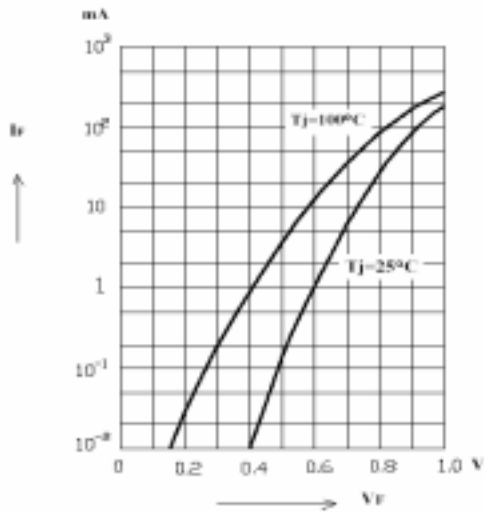
**Electrical Characteristics** (Ratings at 25 ambient temperature unless otherwise specified).

符号 Symbols	参数 Parameter		测试条件 Test Condition	界限 Limits		单位 Unit
				Min	Max	
IR	反向漏电流 Leakage Current	BAV100	$V_R=50V; T_j=25$	---	100	nA
		BAV101	$V_R=100; T_j=25$			
		BAV102	$V_R=150; T_j=25$			
		BAV103	$V_R=200; T_j=25$			
VF	正向电压 Forward Voltage		$I_F=100mA$	---	1.00	V
			$I_F=200mA$		1.25	
TRR1	反向恢复时间 Reverse Recovery Time		$I_F = 30mA$ to $I_R = 30mA$ , $I_{rr} = 3mA, R_L = 100$ .	---	50	nS
Ctot	结电容 Total Capacitance		at $V_R = 0, f = 1MHz$	---	1.5	pF
rf	Dynamic Forward Resistance		$I_F=10mA$	5		



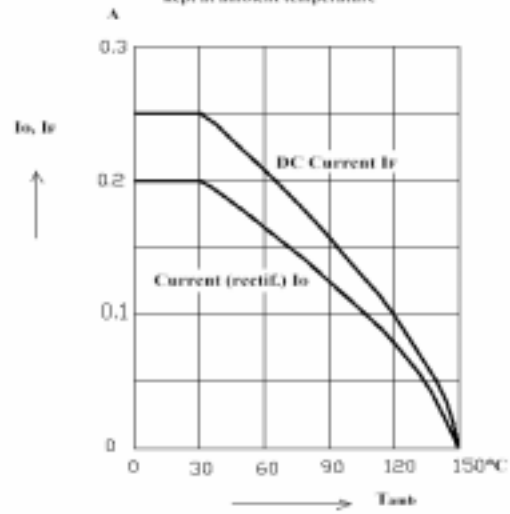
## 特性曲线 Characteristic Curves

Forward characteristics

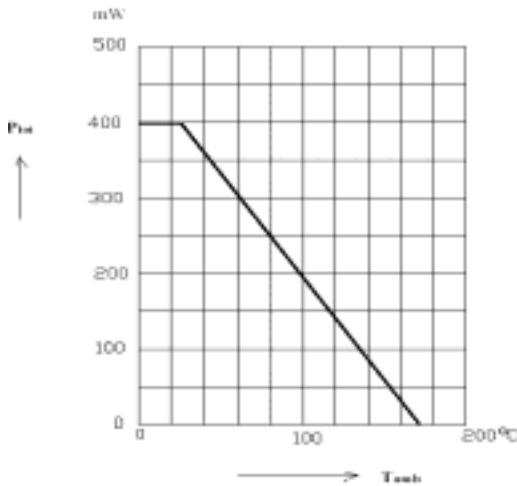


Admissible forward current versus ambient temperature

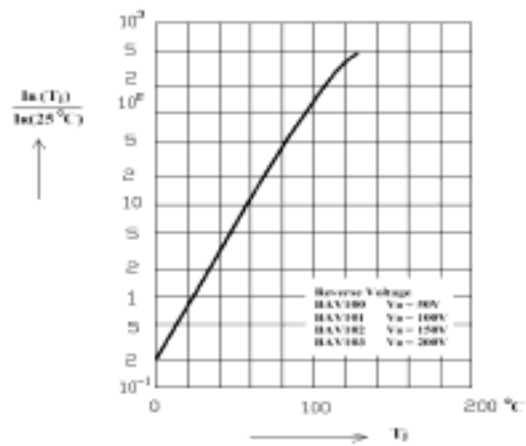
Valid provided that electrodes are kept at ambient temperature



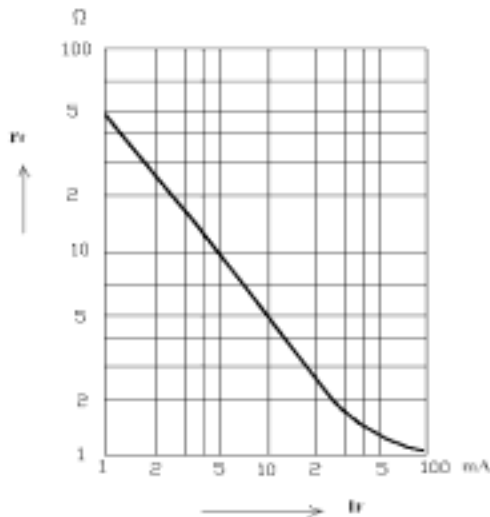
Admissible power dissipation versus ambient temperature



Leakage current versus junction temperature



Dynamic forward resistance versus forward current



Capacitance versus reverse voltage

